ABSTRACT OF THE DISCLOSURE

Provided is a coating liquid for forming a porous film having desirably controlled thickness and having excellent dielectric and mechanical properties, using the conventional semiconductor process. Specifically, provided is a composition for forming a porous film comprising a condensation product and an organic solvent wherein the condensation product is obtained by hydrolysis and condensation, at presence of a basic catalyst, of

one or more silane compounds represented by formula (1): $R^1_kSi(OR^2)_{4-k}$,

and one or more crosslinking agents represented by formla (2): $\{X_j(Y)_{3-j}Si-(L)_m-\}_nMZ_{4-n}$.

Moreover, a method for manufacturing a porous film comprising steps of applying said composition so as to form a film, drying the film and heating the dried film so as to hardent the film, and others are provided.